CEN-U60

PNP SILICON
POWER TRANSISTOR

TO-202 CASE

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CEN-U60 type is a PNP silicon power transistor designed for high voltage amplifier applications. This device is an electrical equivalent to Motorola's MPSU60.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	0.5	A
Power Dissipation	P_D	1.75	W
Power Dissipation (T_C=25°C)	P_D	10	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	70	°C/W
Thermal Resistance	Θ_{JC}	12.5	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=200V		0.2	μA
I_{EBO}	V_{EB}=3.0V		0.1	μA
BV_{CBO}	I_C=100μA	300		V
BV_{CEO}	I_C=1.0mA	300		V
BV_{EBO}	I_E=10μA	5.0		V
$V_{CE(SAT)}$	I_C=20mA, I_B=2.0mA		0.75	V
$V_{BE(SAT)}$	I_C=20mA, I_B=2.0mA		0.90	V
h_{FE}	V_{CE}=10V, I_C=1.0mA	25		
h_{FE}	V_{CE}=10V, I_C=10mA	30		
h_{FE}	V_{CE}=10V, I_C=30mA	30		
f_T	V_{CE}=20V, I_C=10mA, f=100MHz	60		MHz
C_{ob}	V_{CB}=20V, I_E=0, f=1.0MHz		8.0	pF

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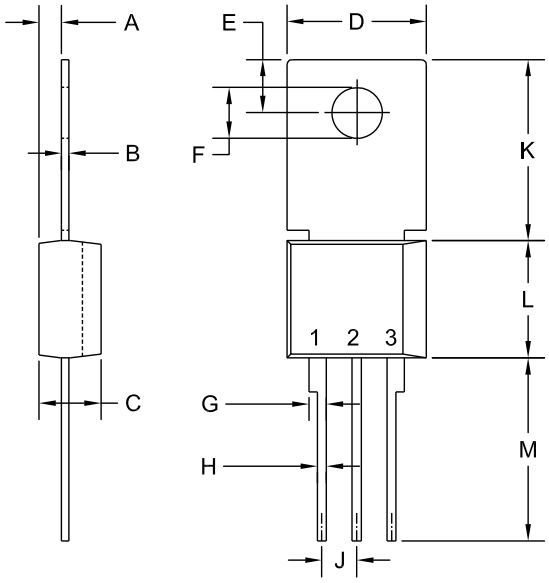
TO-202 CASE - MECHANICAL OUTLINE



R1

LEAD CODE:
1) Emitter
2) Base
3) Collector
Tab is common to pin 3

MARKING:
FULL PART NUMBER

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.055	0.071	1.40	1.80
B	0.016	0.024	0.40	0.60
C	0.173	0.181	4.40	4.60
D	0.374	0.413	9.50	10.50
E	0.146	0.154	3.70	3.90
F (DIA)	0.142	0.150	3.60	3.80
G	0.039	0.055	1.00	1.40
H	0.024	0.031	0.60	0.80
J	0.094	0.106	2.39	2.69
K	0.492	0.551	12.50	14.00
L	0.327	0.346	8.30	8.80
M	0.492	0.531	12.50	13.50

TO-202 (REV: R1)